IN THE CLAIMS:

Please amend the claims as indicated below

(Currently Amended) An optoelectronic sensor for demodulating a modulated
 photon flux (50) comprising:

a semiconductor region (10):

at least two collecting zones (20, 22) present in the semiconductor region (10) and serving for collecting and tapping off minority carriers (11) generated when <u>said</u> a modulated photon flux (50) penetrates into the semiconductor region (10), and the <u>collecting zones (20, 22) being doped inversely with respect to the semiconductor region</u> (10);

characterized by at least two control zones (32, 34) introduced in the semiconductor region (10) and serving for generating a drift field in a manner dependent on a control voltage that can be applied to the control zones (32, 34), the control zones (32, 34) being of the same doping type as the semiconductor region (10).

- 2. (Original) The optoelectronic sensor as claimed in claim 1, wherein the semiconductor region (10) is situated above or in a semiconductor substrate (12), which is doped more highly than the semiconductor region (10).
- 3. (Original) The optoelectronic sensor as claimed in claim 1, wherein the semiconductor region (10) is applied on a dielectric (12).
- (Original) The optoelectronic sensor as claimed in claim 1, wherein the control
 zones (32, 34) are at a greater distance from the midpoint of the sensor than the collecting
 zones (20, 22).
 - (Original) The optoelectronic sensor as claimed in claim 1, wherein the semiconductor region (10) is p-doped.

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- (Currently Amended) The optoelectronic sensor as claimed in claim 1, wherein
 the collecting zones (20, 22) are diffused and doped inversely with respect to the
 semiconductor region (10).
- (Original) The optoelectronic sensor as claimed in claim 1, wherein the collecting zones (20, 22) are produced by local charge transfers in the semiconductor region (10).
 - (Cancelled)
- 10 9. (Cancelled)
 - (Cancelled)
 - 11. (Cancelled)
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- (Cancelled)
- 13. (Currently Amended) A measuring device in particular for 3D distance measurement, comprising
- at least one optoelectronic sensor as claimed in claim 1 one of claims 1 to 12,
 - an optical transmitter for generating a modulated photon flux having a predetermined phase,
 - a device (60) for generating a control voltage, the phase of the control voltage being in a fixed relationship with the phase of the photon flux generated by the transmitter, and
 - an evaluation device (40, 42) assigned to the collecting zones (20, 22) and serving for determining the amplitude and the phase of the modulated photon flux with respect to the phase of the control voltage.